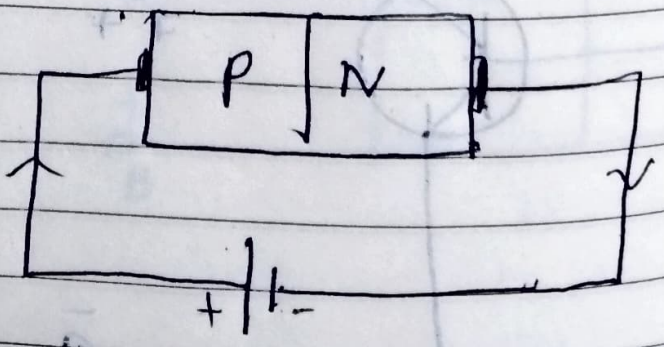
BJT → Bipolar Junction Transistor

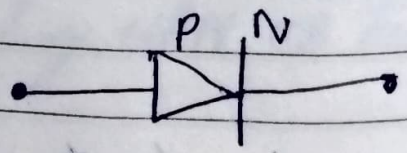
Junction transistors or simply Bipolar transistor (BJT) is a semiconductor device having two junction & three terminals. It is obtained by growing a thin layer of one type of semiconductor in between two thick layers of other similar type of semiconductors

Types of junction Transistors

(1) N-P-N Transistor

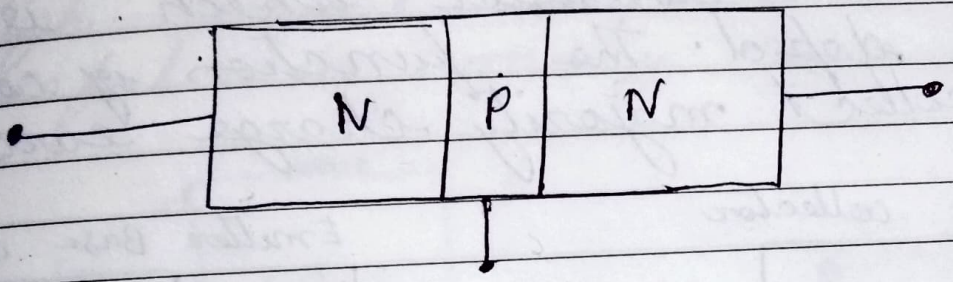
(2) P-N-P Transistor





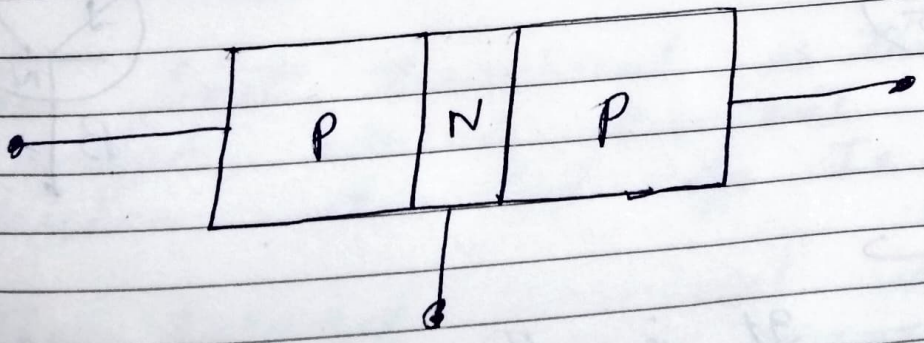
(1) N-P-N Transistors →

A N-P-N transistor is obtained by growing a thin layer of P-type semiconductor in between two relatively thick layers of n type semiconductor



(2) P-N-P Transistors →

A P-N-P transistor is obtained by growing a thin layer of N type semiconductor in between two relatively thick layer of P-Type semiconductor



Main components of Transistor →

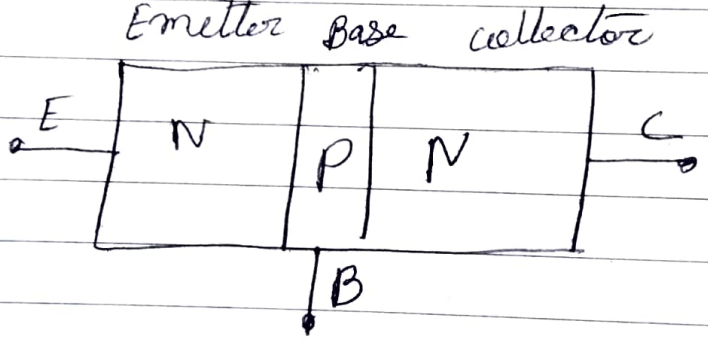
(1) Emitter →

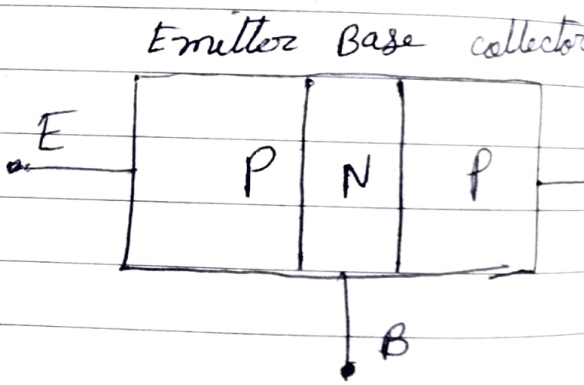
It is left hand side thick layer of moderately size of the transistor which is heavily doped. The function

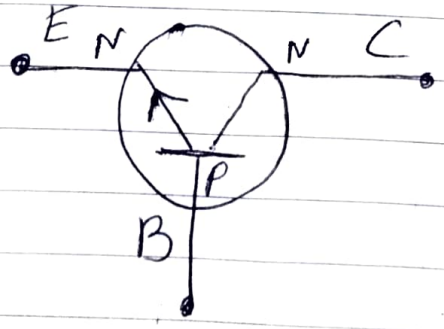
of emitter is to emit majority charge carriers.

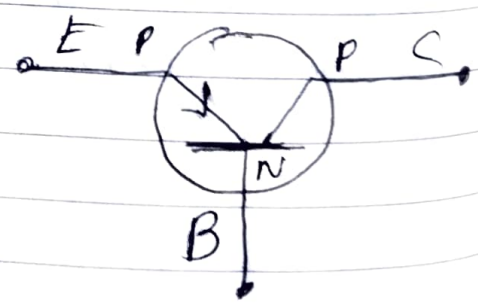
(2) collector →

It is right hand side thick layer of large size than that of emitter of the transistor which is moderately doped. The function of collector is to collect majority charge carriers









(3) Base →

It is the central thin layer of transistor which is lightly doped Base provides the proper interaction between the emitter and collector.